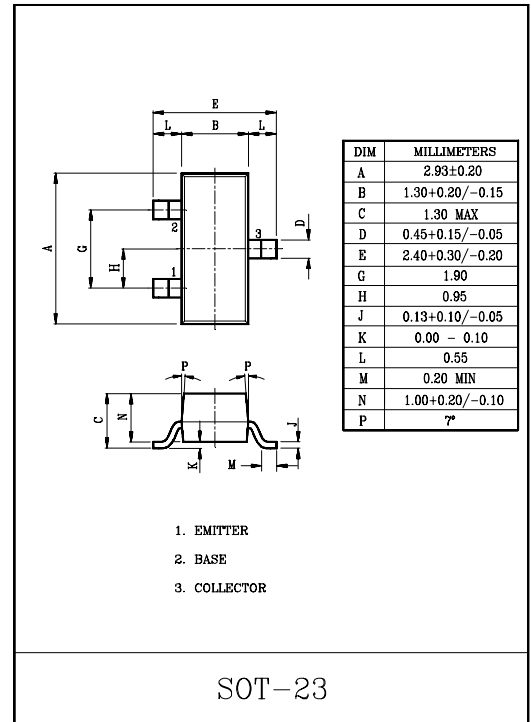


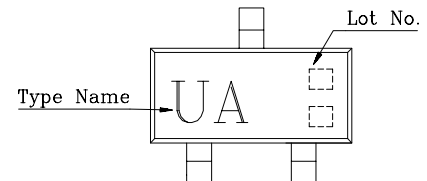
GENERAL PURPOSE HIGH DARLINGTON TRANSISTOR.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	30	V
Emitter-Base Voltage	V <sub>EBO</sub>	10	V
Collector Current	I <sub>C</sub>	400	mA
Collector Power Dissipation	P <sub>C</sub>	350	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55~150	°C



Marking



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =0.1mA	40	-	-	V
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA	30	-	-	V
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-1.0mA	10	-	-	V
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> =40V	-	-	1	μA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =10V	-	-	1	μA
DC Current Gain	h <sub>FE</sub>	I <sub>C</sub> =100mA, V <sub>CE</sub> =2V	30K	-	-	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =1mA	-	-	1	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA	-	1.5	2	V
Current Gain Bandwidth Product	f <sub>T</sub>	I <sub>C</sub> =100mA, f=100MHz, V <sub>CE</sub> =2V	-	220	-	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, f=1MHz	-	5	-	pF

\*Pulse Test : Pulse Width ≤ 300μS, Duty Cycle ≤ 2.0%

# MMBTA517

